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Correction: Epitaxial growth of β-Ga_2O_3 (−201) thin film on four-fold symmetry CeO_2 (001) substrate for heterogeneous integrations

Xiao Tang,*[a] Kuang-Hui Li,[a] Che-Hao Liao,[a] Dongxing Zheng,[b] Chen Liu,[b] Rongyu Lin,[a] Na Xiao,[a] Shibin Krishna,[a] Jose Tauboada[a] and Xiaohang Li*[a]

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Correction for 'Epitaxial growth of β-Ga_2O_3 (−201) thin film on four-fold symmetry CeO_2 (001) substrate for heterogeneous integrations' by Xiao Tang *et al.*, *J. Mater. Chem. C*, 2021, **9**, 15868–15876, DOI: 10.1039/D1TC02852A.

The authors regret the omission of the email address for the co-corresponding author, Xiaohang Li, from the original published article. Their email address is Xiaohang.li@kaust.edu.sa, and the corrected author affiliation details are shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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[a] *Advanced Semiconductor Laboratory, King Abdullah University of Science and Technology (KAUST), Thuwal 23955-6900, Saudi Arabia. E-mail: xiao.tang@kaust.edu.sa, Xiaohang.li@kaust.edu.sa*

[b] *Division of Physical Science and Engineering (PSE), King Abdullah University of Science and Technology (KAUST), Thuwal 23955-6900, Saudi Arabia*